



# 3CT12A

## 主要参数 MAIN CHARACTERISTICS

$I_{T(AV)}$	12A
$V_{DRM}/V_{RRM}$	600V
$I_{GT}$	1-15mA

### 用途

- 半交流开关
- 相位控制

### APPLICATIONS

- Half AC switching
- Phase control

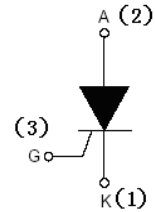
### 产品特性

- 玻璃钝化芯片，高可靠性和一致性
- 低通态电流和高浪涌电流能力
- 环保 RoHS 产品

### FEATURES

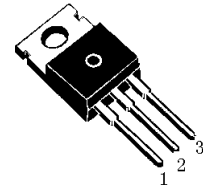
- Glass-passivated mesa chip for reliability and uniform
- Low on-state voltage and High  $I_{TSM}$
- RoHS products

## 封装 Package

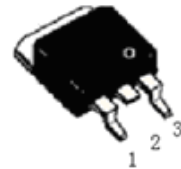


序号 Pin	引线名称 Description
1	阴极 K
2	阳极 A
3	门极 G

### TO-220C



### TO-263



## 订货信息 ORDER MESSAGE

订货型号 Order codes	印记 Marking	无卤素 Halogen Free	封装 Package	包装 Packaging
3CT12A-O-C-N-C	3CT12A	含卤	TO-220C	袋装 Bag
3CT12A-O-C-N-B	3CT12A	含卤	TO-220C	条管 Tube
3CT12A-O-S-B-B	3CT12A	含卤	TO-263	条管 Tube



**绝对最大额定值 ABSOLUTE RATINGS (T<sub>c</sub>=25°C)**

项 目 Parameter	符 号 Symbol	数 值 Value	单 位 Unit
断态重复峰值电压 Repetitive peak off-state voltage	V <sub>DRM</sub>	600	V
反向重复峰值电压 Repetitive peak reverse voltage	V <sub>RRM</sub>	600	V
通态平均电流 Average on-state current ( half sine wave)	I <sub>T(AV)</sub>	12	A
通态方均根电流 On-state RMS current ( all conduction angles )	I <sub>T(RMS)</sub>	18	A
非重复浪涌峰值通态电流 Non- repetitive surge peak on-state current ( half sine wave ,t=10ms)	I <sub>TSM</sub>	200	A
I <sup>2</sup> t for fusing ( t=10ms)	I <sup>2</sup> t	200	A <sup>2</sup> s
门极峰值电流 Peak gate current	I <sub>GM</sub>	5	A
门极峰值电压 Peak gate voltage	V <sub>GM</sub>	5	V
反向门极峰值电压 Peak reverses gate voltage	V <sub>RGM</sub>	5	V
门极峰值功率 Peak gate power	P <sub>GM</sub>	20	W
门极平均功率 Average gate power ( over any 20ms period )	P <sub>G(AV)</sub>	0.5	W
存储温度 Storage temperature	T <sub>stg</sub>	-40~150	°C
操作结温 Operation junction temperature	T <sub>VJ</sub>	125	°C

**静态特性 STATIC CHARACTERISTICS (T<sub>c</sub>=25°C unless otherwise stated)**

项 目 Parameter	符号 Symbol	测试条件 Tests conditions	最小 min	典型 typ	最大 max	单位 Unit
断态峰值重复电流 Peak Repetitive Blocking Current	I <sub>DRM</sub>	V <sub>DM</sub> =V <sub>DRM(MAX)</sub> , T <sub>j</sub> =125°C	-	-	1.0	mA
反向峰值重复电流 Peak Repetitive Reverse Current	I <sub>RRM</sub>	V <sub>RM</sub> =V <sub>RRM(MAX)</sub> , T <sub>j</sub> =125°C	-	-	1.0	mA
峰值通态电压 Peak on-state voltage	V <sub>TM</sub>	I <sub>TM</sub> =40A	-	1.45	1.80	V
门极触发电流 Gate trigger current	I <sub>GT</sub>	V <sub>DM</sub> =12V, I <sub>T</sub> =0.1A	1	4	15	mA
门极触发电压 Gate trigger voltage	V <sub>GT</sub>	V <sub>DM</sub> =12V, I <sub>T</sub> =0.1A	-	0.8	1.5	V
维持电流 Holding current	I <sub>H</sub>	V <sub>DM</sub> =12V, I <sub>GT</sub> =0.1A	-	-	25	mA
擎住电流 Latching current	I <sub>L</sub>	V <sub>DM</sub> =12V, I <sub>GT</sub> =0.1A	-	-	40	mA

**动态特性 DYNAMIC CHARACTERISTICS (T<sub>c</sub>=25°C unless otherwise stated)**

项 目 Parameter	符号 Symbol	测试条件 Tests conditions	最小 min	典型 typ	最大 max	单位 Unit
断态临界电压上升率	dV/dt	V <sub>DM</sub> =67% V <sub>DRM(MAX)</sub> ,	50	200	-	V/μs



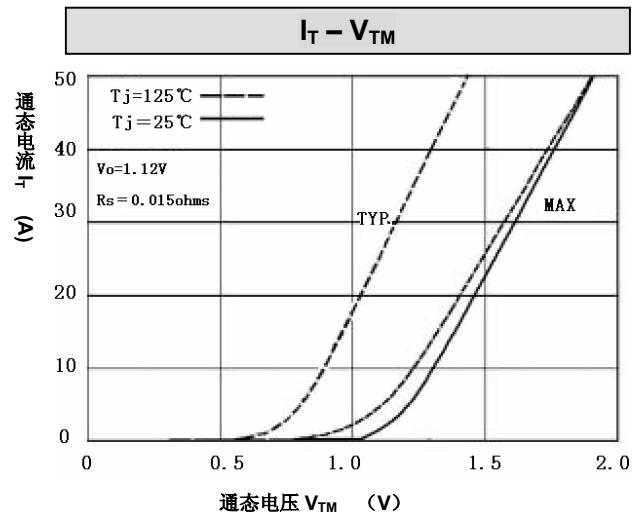
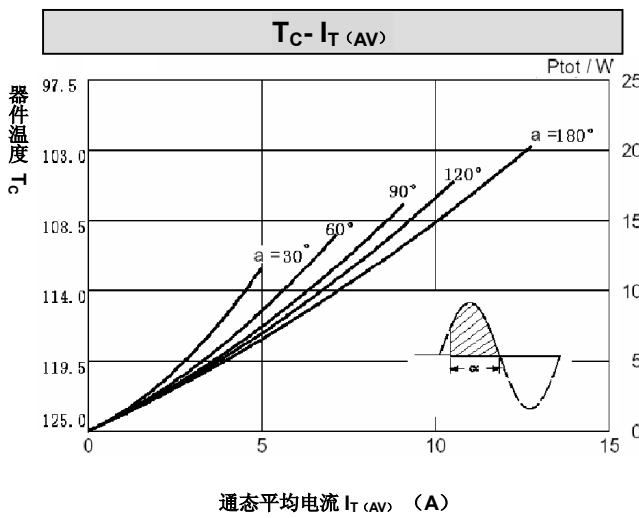


Critical rate of rise of off- state voltage		$T_j=125^\circ\text{C}$				
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### 热特性 THERMAL CHARACTERISTIC

项 目 Parameter	符 号 Symbol	值 value	单位 Unit
结到管壳的热阻 Thermal resistance junction to case	$R_{th(j-c)}$	1.1 max	°C/W
结到环境的热阻 Thermal resistance junction to ambient	$R_{th(j-a)}$	60 typ	

### 特征曲线 ELECTRICAL CHARACTERISTICS (curves)

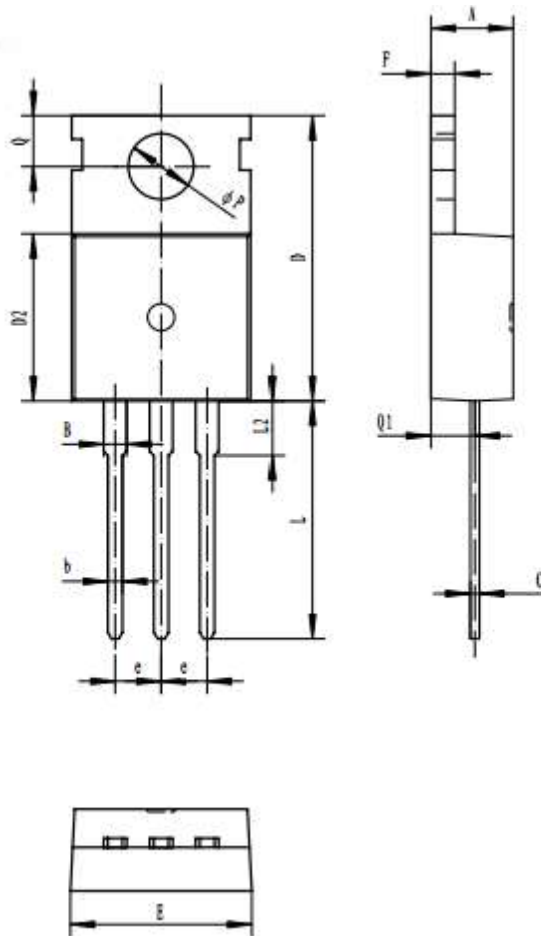




外形尺寸 PACKAGE MECHANICAL DATA

**TO-220C**

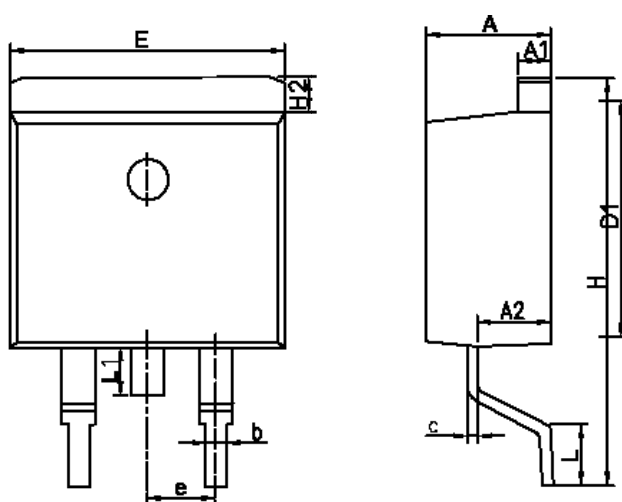
单位 Unit : mm



<b>A</b>	4.30-4.70
<b>B</b>	1.22-1.40
<b>b</b>	0.70-0.95
<b>c</b>	0.40-0.65
<b>D</b>	15.2-16.2
<b>D2</b>	9.00-9.40
<b>E</b>	9.70-10.10
<b>e</b>	2.39-2.69
<b>F</b>	1.25-1.40
<b>L</b>	12.60-13.60
<b>L2</b>	2.80-3.20
<b>Q</b>	2.60-3.00
<b>Q1</b>	2.20-2.60
<b>P</b>	3.50-3.80

**TO-263**

单位 Unit : mm



<b>A</b>	4.30-4.80
<b>A1</b>	1.12-1.42
<b>A2</b>	2.54-2.84
<b>b</b>	0.67-1.00
<b>c</b>	0.29-0.52
<b>D1</b>	8.40-9.00
<b>E</b>	9.80-10.46
<b>e</b>	2.54BSC
<b>H</b>	14.00-16.00
<b>H2</b>	1.12-1.45
<b>L</b>	1.50-3.10
<b>L1</b>	1.45-1.70



**注意事项**

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3. 在电路设计时请不要超过器件的绝对最大额定值，否则会影响整机的可靠性。
4. 本说明书如有版本变更不另外告知

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2. We strongly recommend customers check carefully on the trademark when buying our product, if there is any question, please don't be hesitate to contact us.
3. Please do not exceed the absolute maximum ratings of the device when circuit designing.
4. Jilin Sino-microelectronics co., Ltd reserves the right to make changes in this specification sheet and is subject to change without prior notice.

**联系方式****吉林华微电子股份有限公司**

公司地址：吉林省吉林市深圳街 99 号

邮编：132013

总机：86-432-64678411

传真：86-432-64665812

网址：[www.hwdz.com.cn](http://www.hwdz.com.cn)

**市场营销部**

地址：吉林省吉林市深圳街 99 号

邮编：132013

电话：86-432-64675588

64675688

64678411

传真：86-432-64671533

**CONTACT****JILIN SINO-MICROELECTRONICS CO., LTD.**

ADD: No.99 Shenzhen Street, Jilin City, Jilin Province, China.

Post Code: 132013

Tel: 86-432-64678411

Fax: 86-432-64665812

Web Site: [www.hwdz.com.cn](http://www.hwdz.com.cn)

**MARKET DEPARTMENT**

ADD: No.99 Shenzhen Street, Jilin City, Jilin Province, China.

Post Code: 132013

Tel: 86-432-64675588

64675688

64678411

Fax: 86-432-64671533

**附录 (Appendix) : 修订记录 (Revision History)**

日期 Date	旧版本 Last Rev.	新版本 New Rev.	修订内容 Description of Changes
2009-11-3	200901D	200911E	中英文格式改版，修改电话号码
2010-9-6	200911E	201009F	修改 TO-220C 外形
2011-9-1	201009F	201109G	修改 TO-263 外形





2015-10-22	201109G	201510H	修订外形尺寸、排版
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